



# PSMN1R9-80SSE

N-channel 80 V, 1.9 mOhm MOSFET with enhanced SOA in LFPAK88

16 December 2022

Product data sheet

## 1. General description

N-channel enhancement mode MOSFET in a LFPAK88 package qualified to 175 °C. Part of Nexpria's "ASFETs for hotswap" portfolio, the PSMN1R9-80SSE delivers very low  $R_{DSon}$  and a very strong linear-mode (SOA) performance in a high-reliability copper-clip LFPAK88 package.

PSMN1R9-80SSE complements the latest "hot-swap" controllers – robust enough to withstand substantial inrush currents during turn-on, low  $R_{DSon}$  to minimize  $I^2R$  losses and deliver optimum efficiency when turned fully ON.

## 2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Low  $R_{DSon}$  for low  $I^2R$  conduction losses
- LFPAK88 package for applications that demand the highest performance and reliability

## 3. Applications

- Hot swap
- Load switch
- Soft start
- E-fuse
- Telecommunication and computing systems based on a 48 V backplane/supply rail

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$		-	-	80	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 2</a>		-	-	286	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a>		-	-	340	W
$T_j$	junction temperature			-55	-	175	$^{\circ}\text{C}$
<b>Static characteristics</b>							
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 12</a>		-	1.6	1.9	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 100\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 13</a>		-	2.6	3	$\text{m}\Omega$
<b>Dynamic characteristics</b>							
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}; V_{DS} = 40\text{ V}; V_{GS} = 10\text{ V}$ ;		7	23	53	nC
$Q_{G(tot)}$	total gate charge	$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		77	155	232	nC
<b>Avalanche ruggedness</b>							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 90\text{ A}; V_{sup} \leq 80\text{ V}; R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; unclamped; $t_p = 179\text{ }\mu\text{s}$ ; <a href="#">Fig. 4</a>	[1]	-	-	840	mJ

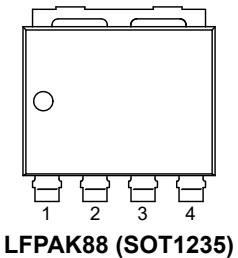
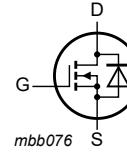
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Source-drain diode</b>							
Q <sub>r</sub>	recovered charge	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 40 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 18</a>	[2]	-	60	-	nC

[1] Protected by 100% test

[2] includes capacitive recovery

## 5. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		
3	S	source		
4	S	source		
mb	D	mounting base; connected to drain	 LFPAK88 (SOT1235)	 mbb076

## 6. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PSMN1R9-80SSE	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235

## 7. Marking

**Table 4. Marking codes**

Type number	Marking code
PSMN1R9-80SSE	X1E9S80S

## 8. Limiting values

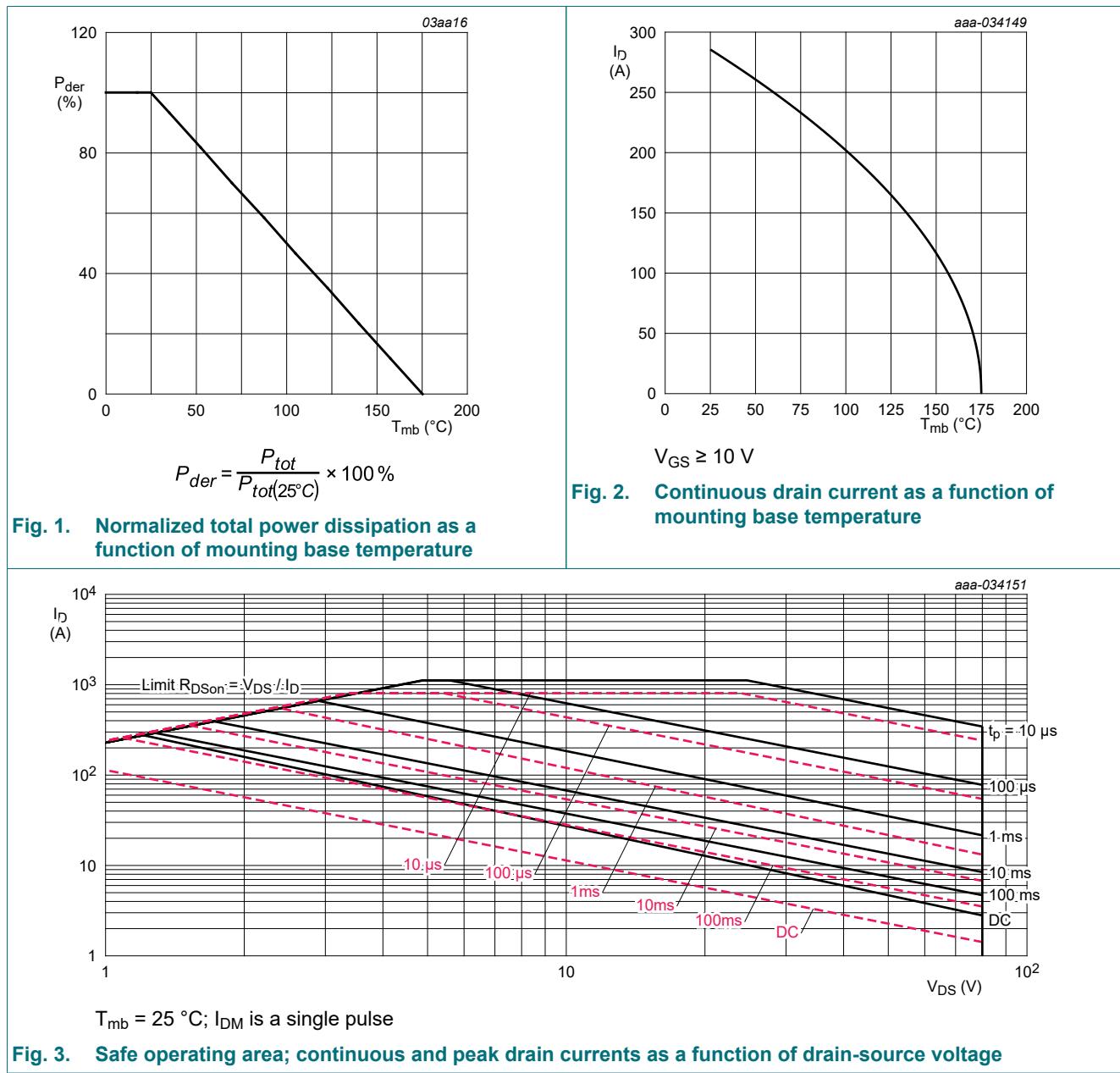
**Table 5. Limiting values**

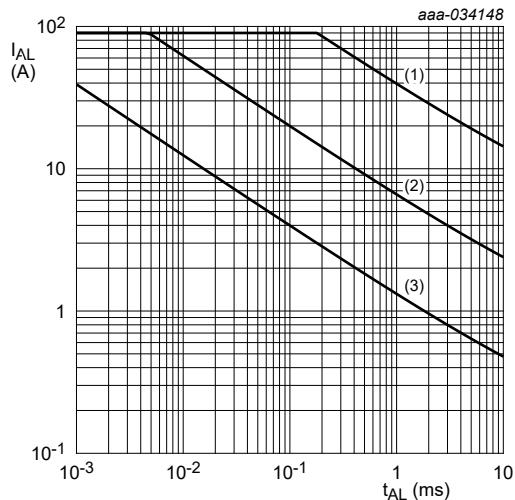
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	80	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	80	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>		-	340	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>		-	286	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <a href="#">Fig. 2</a>		-	202	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 3</a>		-	1142	A
T <sub>stg</sub>	storage temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
$T_j$	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
<b>Source-drain diode</b>						
$I_s$	source current	$T_{mb} = 25$ °C		-	286	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C		-	1142	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 90$ A; $V_{sup} \leq 80$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped; $t_p = 179$ µs; <a href="#">Fig. 4</a>	[1]	-	840	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} = 80$ V; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $R_{GS} = 50$ Ω; <a href="#">Fig. 4</a>	[1]	-	90	A

[1] Protected by 100% test





(1)  $T_j \text{ (init)} = 25 \text{ }^\circ\text{C}$ ; (2)  $T_j \text{ (init)} = 150 \text{ }^\circ\text{C}$ ; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>	-	0.2	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	<a href="#">Fig. 6</a> <a href="#">Fig. 7</a>	-	35	-	K/W

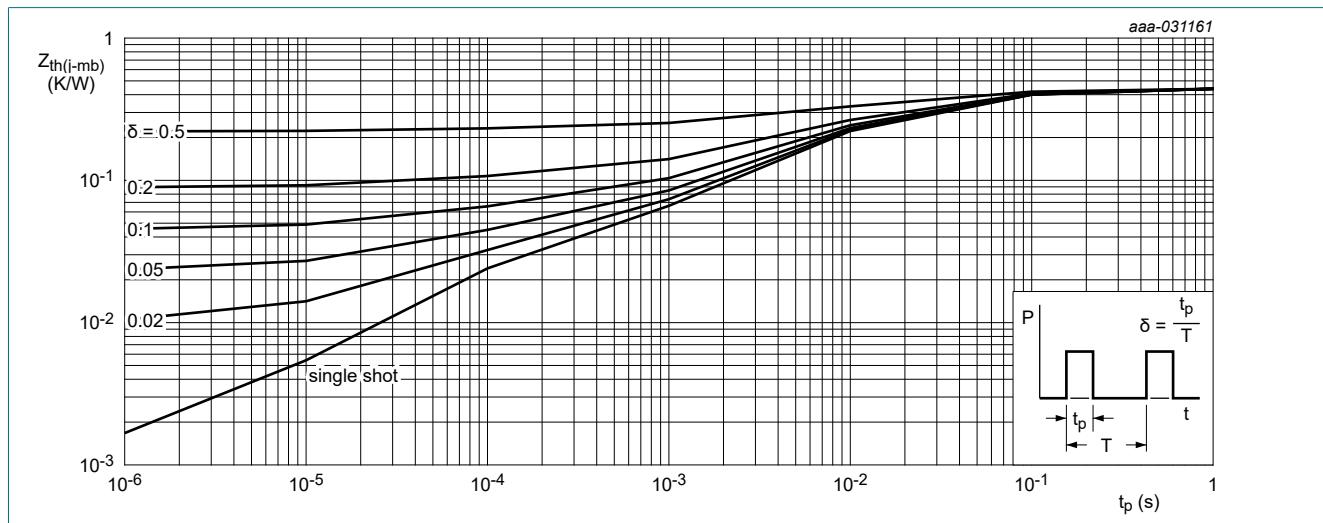
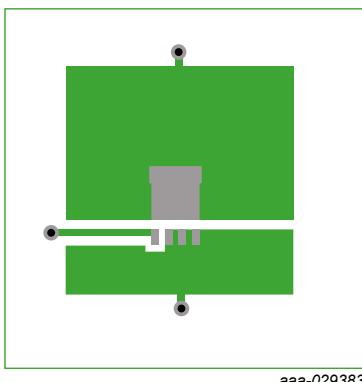
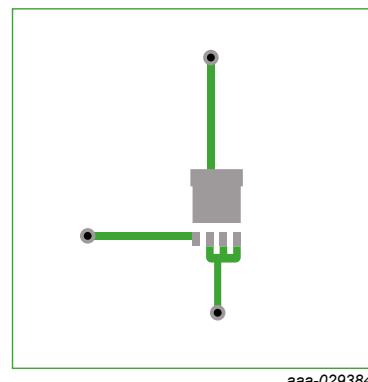


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration



Copper square 25.4 mm x 25.4 mm; 70  $\mu$ m thick on FR4 board

**Fig. 6. PCB layout for resistance from junction to ambient**



70  $\mu$ m thick copper on FR4 board

**Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient**

## 10. Characteristics

**Table 7. Characteristics**

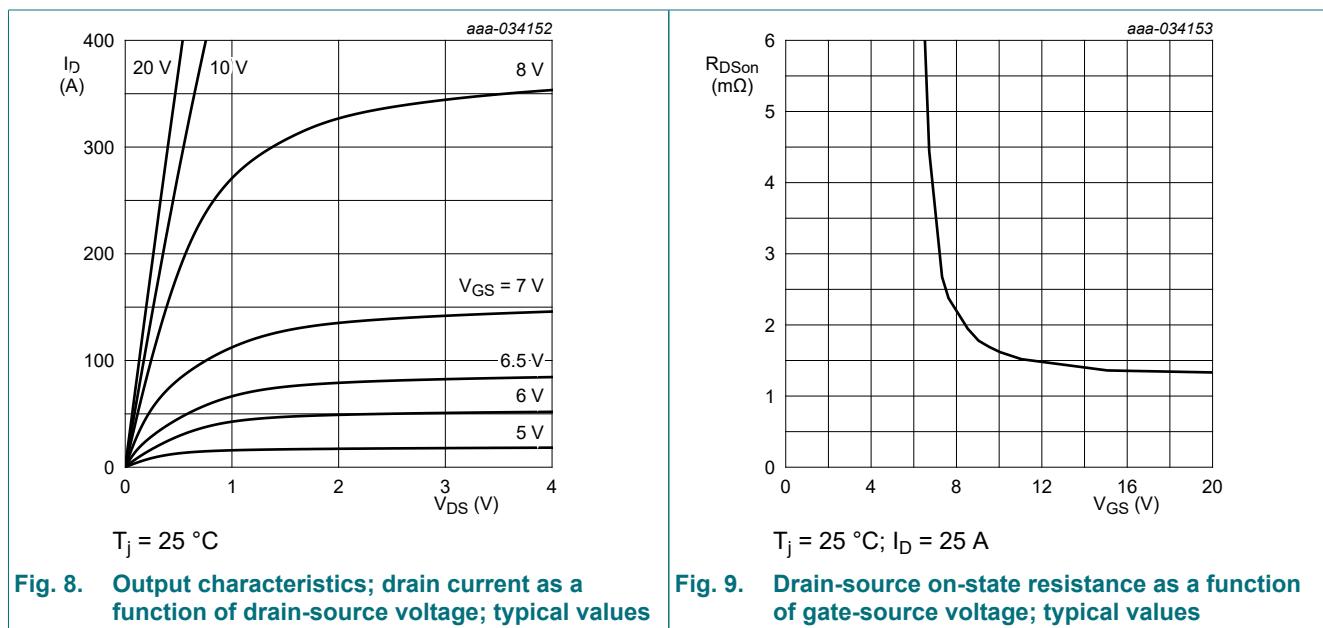
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25^\circ C$ $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55^\circ C$		80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25^\circ C$ ; <a href="#">Fig. 11</a> $I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175^\circ C$ $I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55^\circ C$	2	2.6	3.6	3.6	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25^\circ C \leq T_j \leq 150^\circ C$		-	-6.4	-	mV/K
$I_{DSS}$							
$I_{DSS}$	drain leakage current	$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25^\circ C$	-	0.02	1	1	$\mu A$
		$V_{DS} = 16 V; V_{GS} = 0 V; T_j = 125^\circ C$	-	3	100	100	$\mu A$
$I_{GSS}$							
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25^\circ C$	-	2	100	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25^\circ C$	-	2	100	100	nA
$R_{DSon}$							
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 25^\circ C$ ; <a href="#">Fig. 12</a>	-	1.6	1.9	1.9	$m\Omega$
		$V_{GS} = 10 V; I_D = 25 A; T_j = 100^\circ C$ ; <a href="#">Fig. 13</a>	-	2.6	3	3	$m\Omega$
		$V_{GS} = 10 V; I_D = 25 A; T_j = 175^\circ C$ ; <a href="#">Fig. 13</a>	-	-	4.2	4.2	$m\Omega$
$R_G$	gate resistance	$f = 1 MHz; T_j = 25^\circ C$	0.8	1.6	3.2	3.2	$\Omega$
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$		total gate charge	$I_D = 25 A; V_{DS} = 40 V; V_{GS} = 10 V; T_j = 25^\circ C$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	77	155	232	nC
			$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25^\circ C$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	83	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	36	60	84	nC
$Q_{GS(\text{th})}$	pre-threshold gate-source charge		-	34	-	nC
$Q_{GS(\text{th-pl})}$	post-threshold gate-source charge		-	26	-	nC
$Q_{GD}$	gate-drain charge		7	23	53	nC
$V_{GS(\text{pl})}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	5.2	-	V
$C_{iss}$	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 0.5 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a>	7340	12235	17140	pF
$C_{oss}$	output capacitance		1710	2843	4560	pF
$C_{rss}$	reverse transfer capacitance		7	64	169	pF
$t_{d(\text{on})}$	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 1.6 \Omega; V_{GS} = 10 \text{ V}; R_{G(\text{ext})} = 5 \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	46	-	ns
$t_r$	rise time		-	42	-	ns
$t_{d(\text{off})}$	turn-off delay time		-	79	-	ns
$t_f$	fall time		-	46	-	ns

**Source-drain diode**

$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a>	-	0.78	1	V
$t_{rr}$	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 18</a>	-	54	-	ns
$Q_r$	recovered charge	[1]	-	60	-	nC

[1] includes capacitive recovery



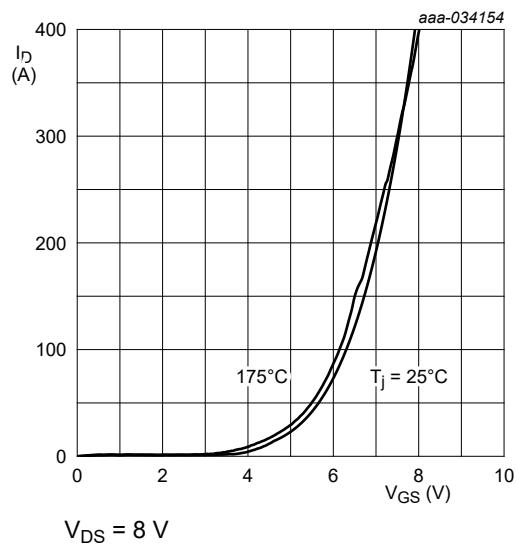


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

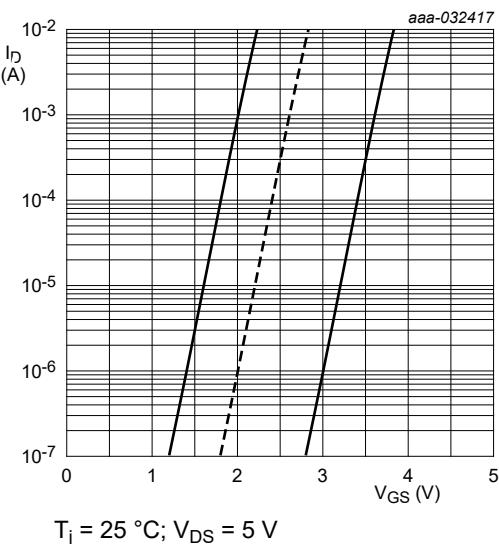


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

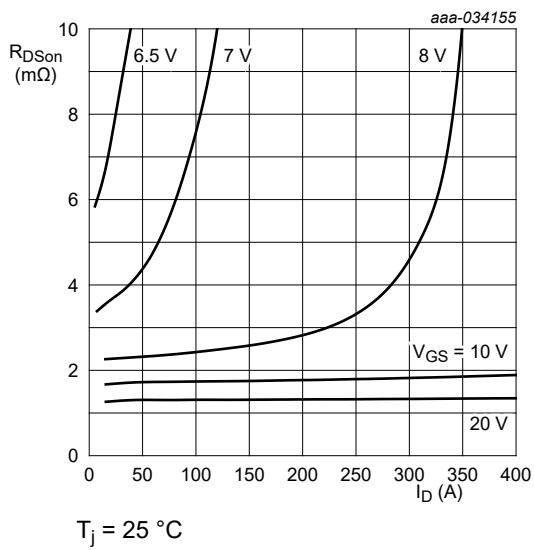


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

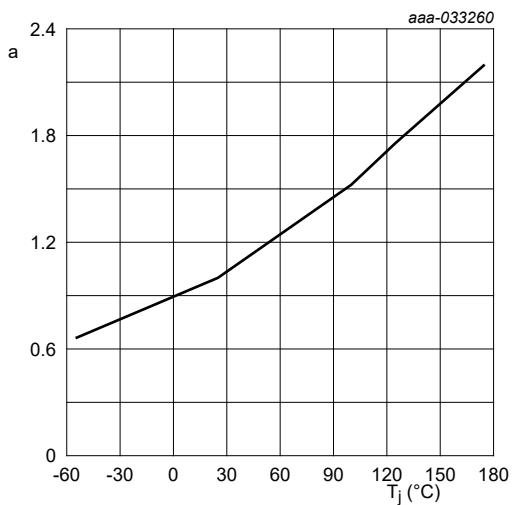


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

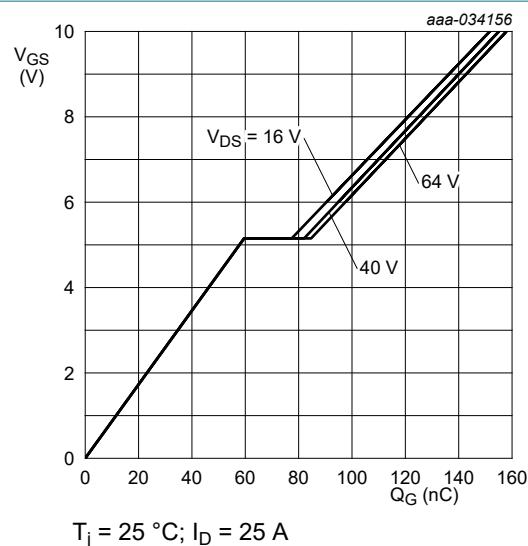


Fig. 14. Gate-source voltage as a function of gate charge; typical values

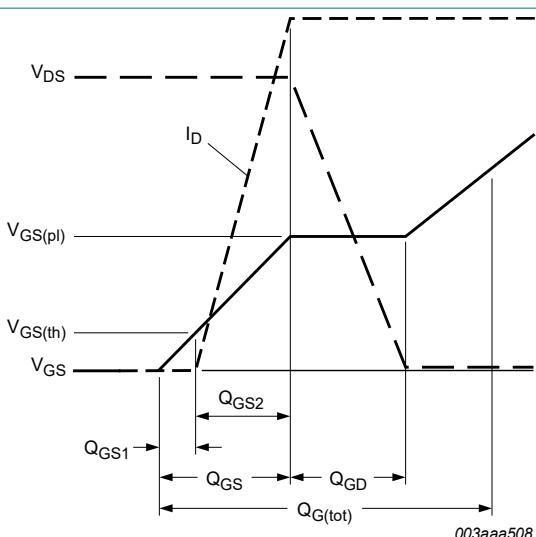


Fig. 15. Gate charge waveform definitions

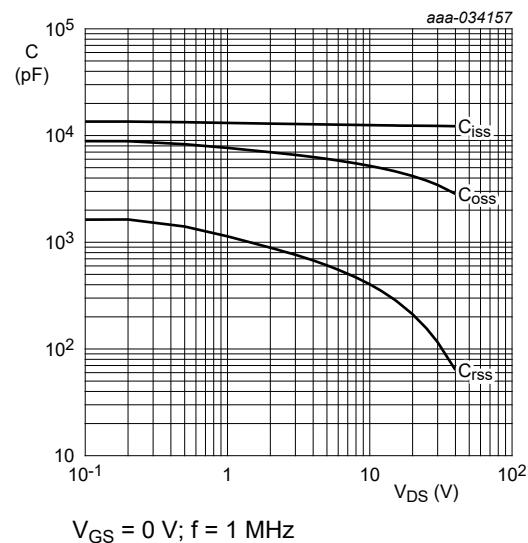


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

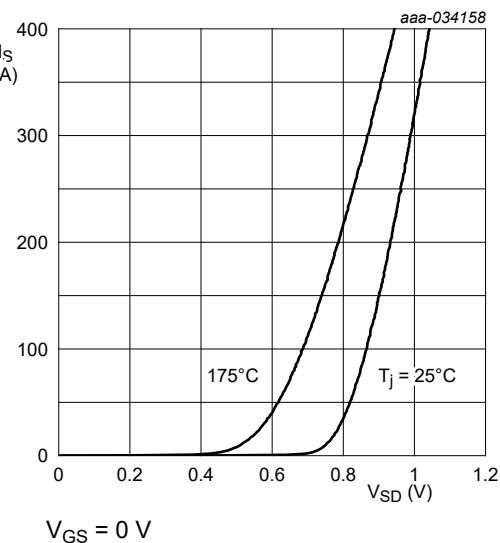


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

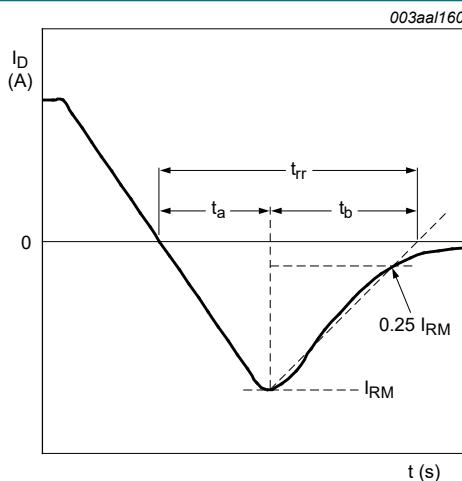
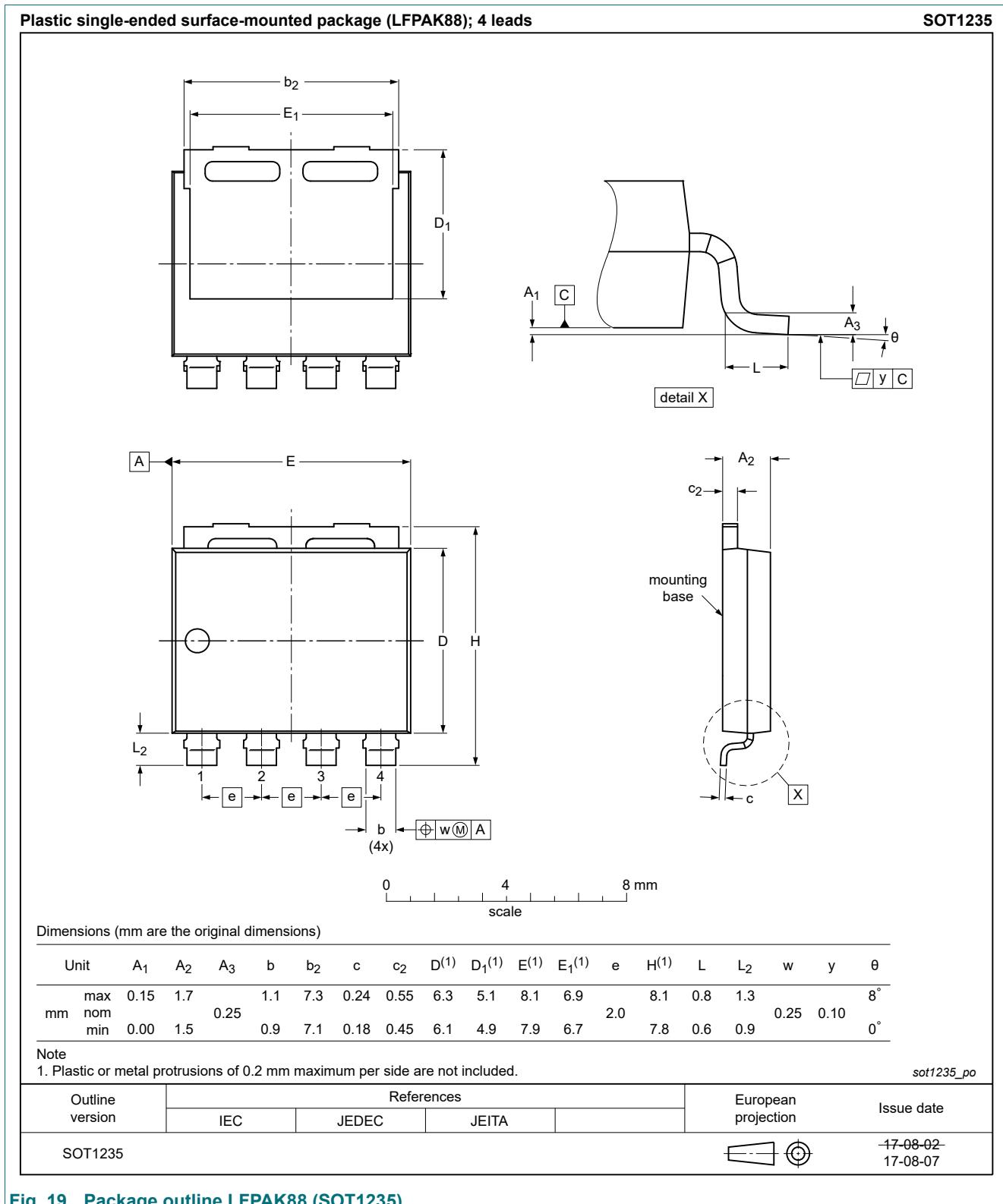


Fig. 18. Reverse recovery timing definition

## 11. Package outline



## 12. Soldering

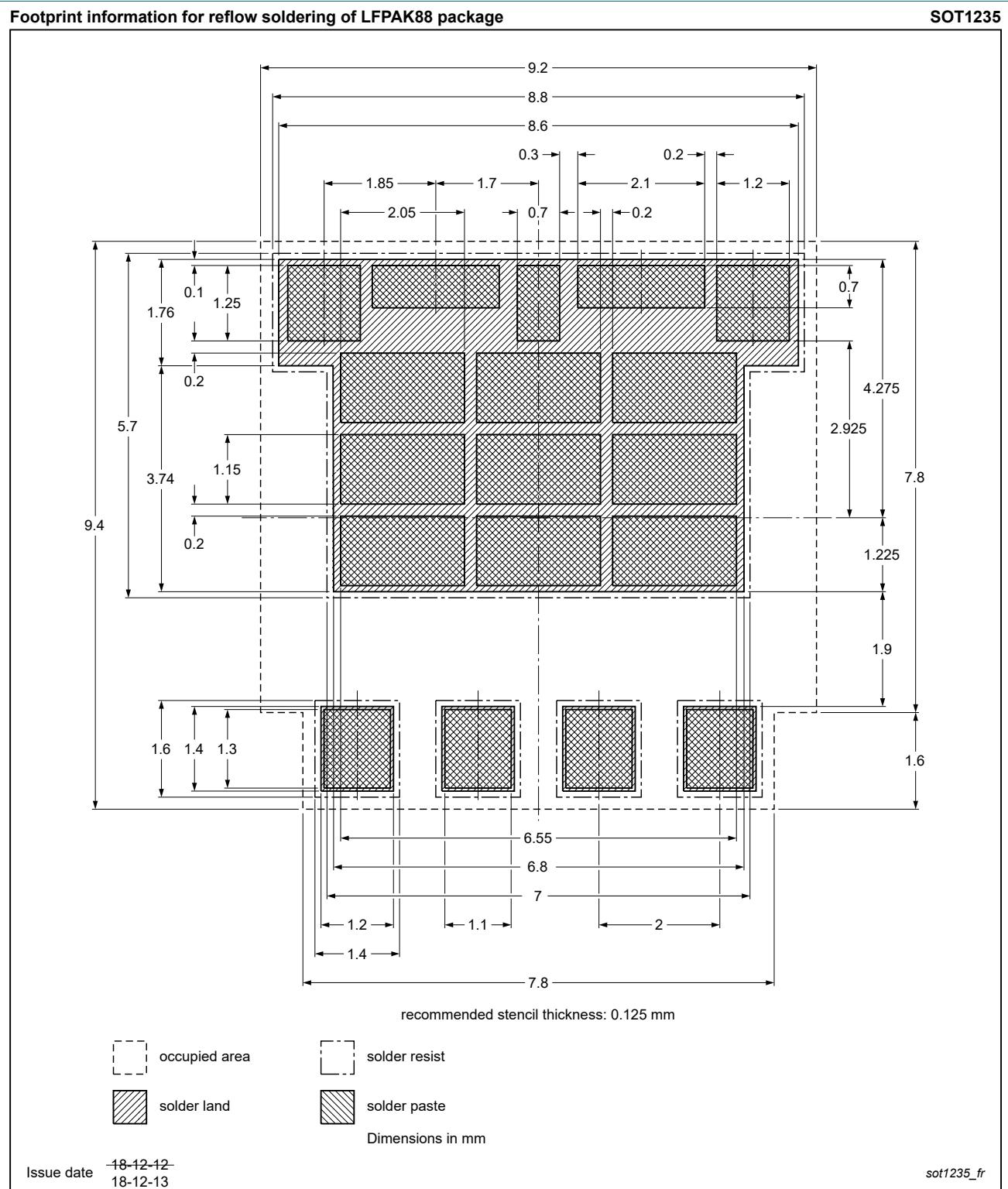


Fig. 20. Reflow soldering footprint for LFPAK88 (SOT1235)

## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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